	Tentative	DRA4523Y		
		Total pages	page	

DRA4523Y

Silicon PNP epitaxial planar type

For digital circuits

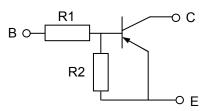
Marking Symbol : SK

Package Code : NS-B1-B

Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	VCBO	-50	V	
Collector-emitter voltage (Base open)	VCEO	-50	V	
Collector current	IC	-500	mA	
Total power dissipation	PT	300	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	С°	

Internal Connection



Resistance	R1	2.2	kΩ	
value	R2	10	kΩ	
Pin name	1.	Emitter		
	2.	Collector		
	3.	Base		

Electrical Characteristics Ta = 25 °C±3 °C

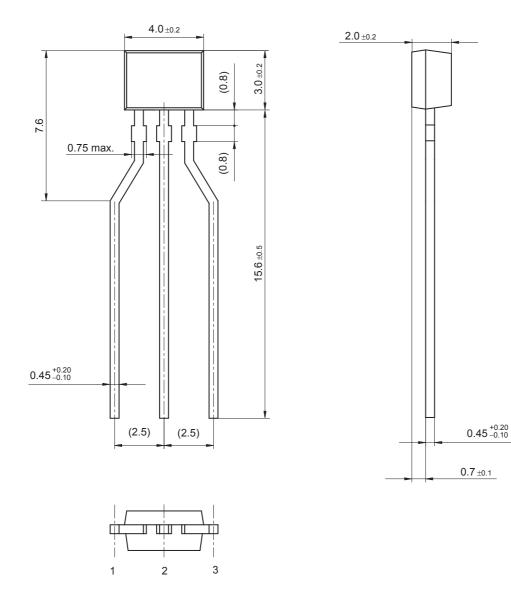
	•				
Symbol		Min	Тур	Max	Unit
VCBO	IC = -10 μA, IE = 0	-50			V
VCEO	IC = -2 mA, IB = 0	-50			V
ICBO	VCB = -50 V, IE = 0			-1	μA
ICEO	VCE = -50 V, IB = 0			-1	μA
IEBO	VEB = -6 V, IC = 0			-1	mA
hFE	VCE = -10 V, IC = -100 mA	60			-
VCE(sat)	IC = -100 mA, IB = -5 mA			-0.25	V
Vi(on)	VCE = -0.2 V, IC = -50 mA	-1.9			V
Vi(off)	VCE = -5 V, IC = -100 μA			-0.4	V
R1		-30%	2.2	+30%	kΩ
R1/R2		0.17	0.22	0.27	-
	VCEO ICBO ICEO IEBO hFE VCE(sat) Vi(on) Vi(off) R1	VCBO IC = -10 μ A, IE = 0 VCEO IC = -2 mA, IB = 0 ICBO VCB = -50 V, IE = 0 ICEO VCE = -50 V, IB = 0 IEBO VEB = -6 V, IC = 0 hFE VCE = -10 V, IC = -100 mA VCE(sat) IC = -100 mA, IB = -5 mA Vi(on) VCE = -0.2 V, IC = -50 mA Vi(off) VCE = -5 V, IC = -100 μ A	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	VCBO IC = $-10 \ \mu$ A, IE = 0 -50 VCEO IC = $-2 \ m$ A, IB = 0 -50 ICBO VCB = $-50 \ V$, IE = 0 -50 ICEO VCE = $-50 \ V$, IB = 0 -50 IEBO VEB = $-6 \ V$, IC = 0 -50 hFE VCE = $-10 \ V$, IC = $-100 \ m$ A 60 VCE(sat) IC = $-100 \ m$ A, IB = $-5 \ m$ A -1.9 Vi(on) VCE = $-5 \ V$, IC = $-100 \ \mu$ A -30% R1 -30% 2.2	VCBO IC = -10 μ A, IE = 0 -50 -50 VCEO IC = -2 mA, IB = 0 -50 -1 ICBO VCE = -50 V, IE = 0 -1 -1 ICEO VCE = -50 V, IB = 0 -1 -1 IEBO VEB = -6 V, IC = 0 -1 -1 hFE VCE = -10 V, IC = -100 mA 60 -1 VCE(sat) IC = -100 mA, IB = -5 mA -0.25 -0.25 Vi(on) VCE = -0.2 V, IC = -50 mA -1.9 -0.4 R1 -30% 2.2 +30%

Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

Packing Radial type : 5 000 pcs / carton

NS-B1-B

Unit: mm



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